

VS-HOT200C080 200 A, 80 V Power MOSFET Module

Saves Space, Lowers Conduction Losses, and Increases Reliability in MHEVs and LEVs



ADVANTAGE

Integrated device features half-bridge MOSFETs with best in class $R_{DS(ON)}$ in compact transfer-mold FlatPAK HC0 package

KEY PRODUCT FEATURES

- ✓ Insulated 30 mm x 22.8 mm transfer-mold FlatPAK HC0 package
- ✓ Drain to source voltage: 80 V
- ✓ On-resistance, Q1 (chip level): 0.45 mΩ typical
- ✓ Continuous drain current: 195 A at 80 °C
- ✓ Electrically isolated, exposed DBC substrate
- ✓ Operating temperature range: -40 °C to +150 °C
- ✓ Qualified according to AQG-324 guidelines



MARKETS AND APPLICATIONS



MOBILITY

- Automotive electrification (belt-start generators / recuperation systems for MHEVs)
- Micro mobility (48 V traction inverters)

ADDITIONAL BENEFITS

- To increase efficiency, the low on-resistance of the power module's MOSFETs reduces conduction losses by 32 % compared to competing solutions
- The VS-HOT200C080 integrates 80 V MOSFETs in a half-bridge configuration, a shunt resistor for current reading, bypass capacitors for improved switching performance, and an NTC for temperature sensing
- The device reduces board space requirements by up to 15 % compared to standard discrete solutions

RESOURCES



[Order Samples](#)



[Product Page](#)



[Contact Us Americas](#)



[Contact Us Asia](#)



[Contact Us Europe](#)